

IN THE CLAIMS:

Please amend claims 81 and 84 as follows:

1-80. (Canceled)

81. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

providing a metal substrate having a front surface, a rear surface, first grooves on the front surface partitioning the front surface in parts, second grooves on the rear surface, each of the second grooves being arranged directly opposite to one of the first grooves across the metal substrate;

providing a semiconductor chip having a front surface, a rear surface, electrodes formed on the front surface;

fixing the semiconductor chip on the front surface of the metal substrate;

forming a plurality of rows of external electrodes in an area of the front surface of the metal substrate and between an edge of the semiconductor chip and an edge of the semiconductor device;

electrically connecting the electrodes of the semiconductor chip with said external electrodes formed in ~~parts of~~ the front surface of the metal substrate by conductive wires, respectively;

forming a resin body which seals the semiconductor chip, the conductive wires, and said external electrodes formed in ~~the parts of the~~ front surface of the metal substrate; and

after the resin body forming step, etching the rear surface of the metal substrate so as to expose bottoms of the second grooves and electrically isolating said external electrodes formed in ~~the parts of~~ the front surface of the metal substrate from one another.

82. (Original) The method of manufacturing a semiconductor device according to claim 81, wherein the etching step involves maintaining parts of the rear surface directly opposite to the parts of the front surface across the metal substrate un-etched so as to protrude therefrom at the bottoms of the second grooves.

83. (Original) The method of manufacturing a semiconductor device according to claim 82, wherein the etching step involves etching the rear surface of the metal substrate by immersing the metal substrate in an etching solution.
84. (Currently Amended) The method of manufacturing a semiconductor device according to claim 83, wherein the etching step involves etching ~~all over~~ all over the rear surface of the metal substrate by the etching solution.